

PNP Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61. See MPSA64 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current - Continuous	1.2	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		MPSA65	*MMBTA65	**PZTA65	
PD	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

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PNP Darlington Transistor (continued)

continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	ARACTERISTICS				
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{B} = 0$	30		V
I _{сво}	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		100	nA
				100	nA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 8.0 V, I_{C} = 0$			

h _{FE}	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	50,000		
		$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	20,000		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 0.1 mA		1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I_{C} = 100 mA, V_{CE} = 5.0 V		2.0	V

SMALL SIGNAL CHARACTERISTICS

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f _T	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 100 MHz	100	MHz
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*Pulse Test: Pulse Width $\leq 300~\mu s,~\text{Duty}~\text{Cycle} \leq 2.0\%$

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